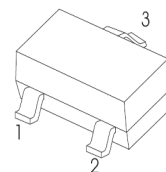


PNP Silicon Epitaxial Planar Transistor

FEATURES

- High voltage and high current
- Excellent h_{FE} Linearity
- Complementary to C1815

SOT-23



1. BASE
2. EMITTER
3. COLLECTOR

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

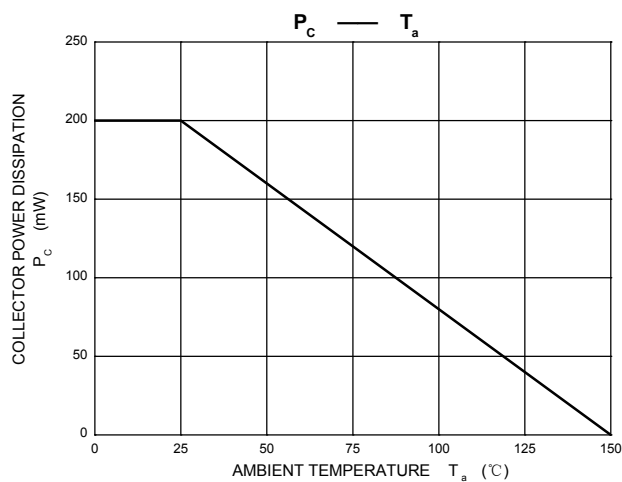
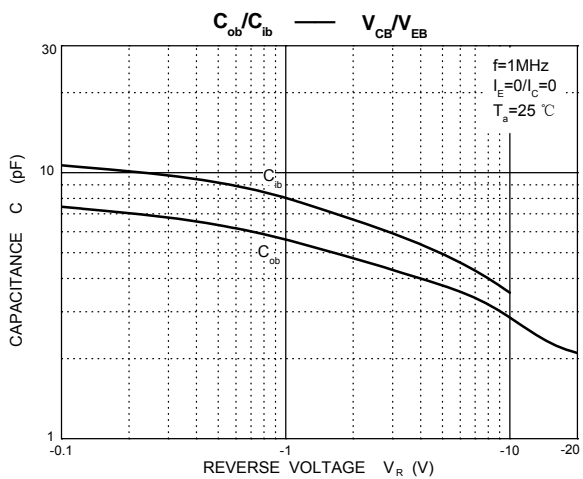
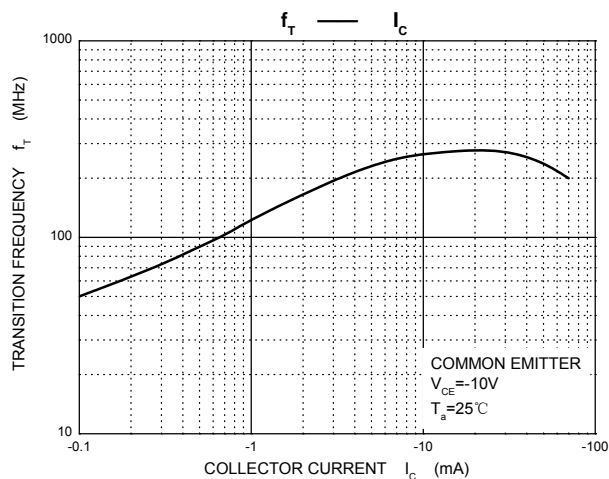
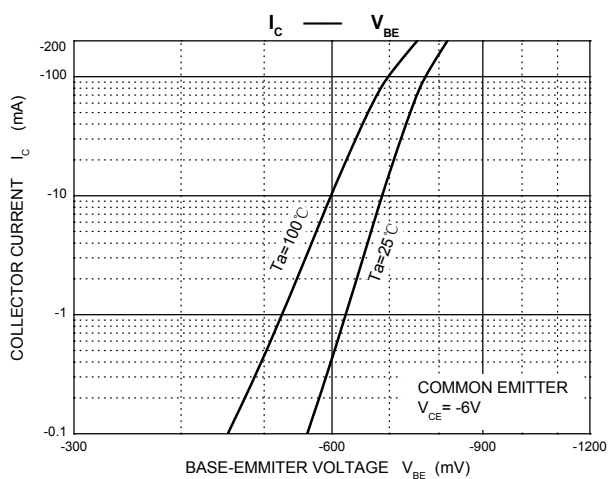
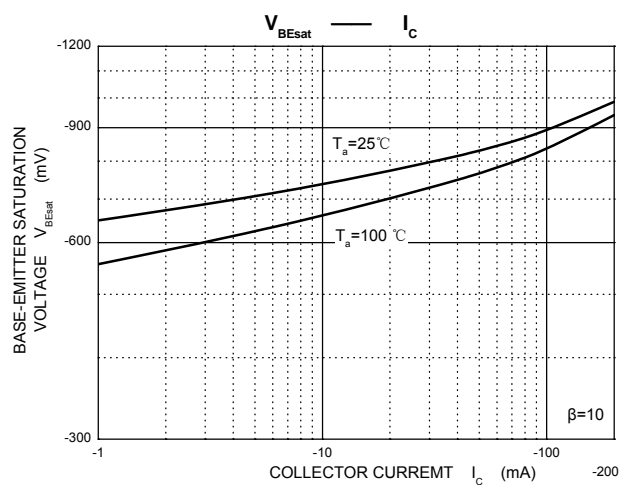
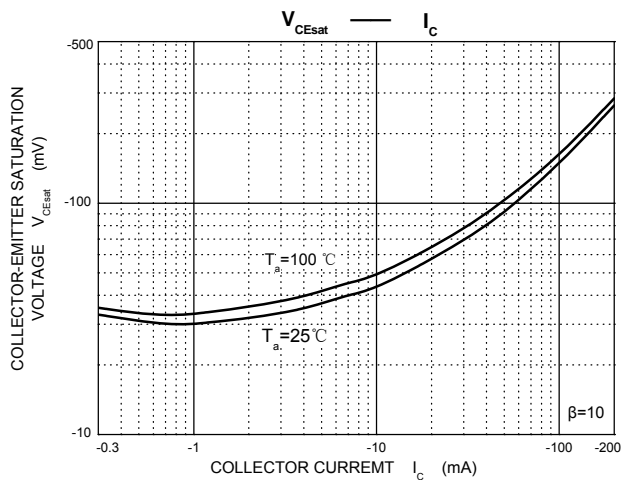
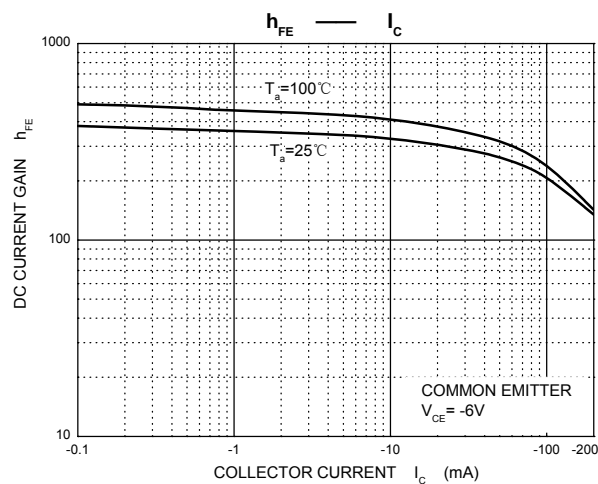
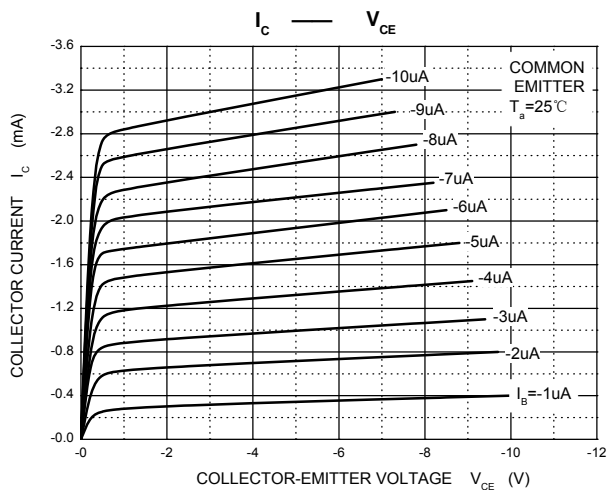
| Symbol | Parameter | Value | Unit |
|-----------|-------------------------------|----------|--------------------|
| V_{CBO} | Collector-Base Voltage | -50 | V |
| V_{CEO} | Collector-Emitter Voltage | -50 | V |
| V_{EBO} | Emitter-Base Voltage | -5 | V |
| I_C | Collector Current -Continuous | -150 | mA |
| P_C | Collector Power Dissipation | 200 | mW |
| T_J | Junction Temperature | 150 | $^{\circ}\text{C}$ |
| T_{stg} | Storage Temperature | -55~+150 | $^{\circ}\text{C}$ |

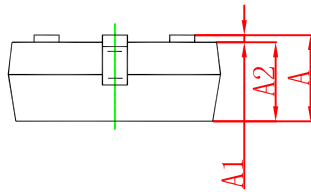
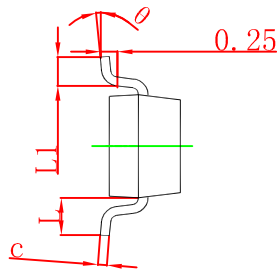
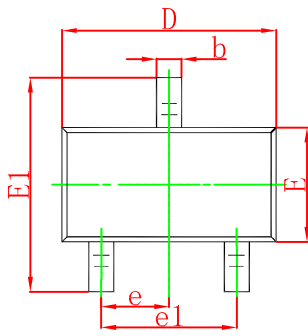
ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

| Parameter | Symbol | Test conditions | Min | Typ | Max | Unit |
|--------------------------------------|---------------|---|-----|-----|------|---------------|
| Collector-base breakdown voltage | $V_{(BR)CBO}$ | $I_C = -100\mu\text{A}, I_E = 0$ | -50 | | | V |
| Collector-emitter breakdown voltage | $V_{(BR)CEO}$ | $I_C = -0.1\text{mA}, I_B = 0$ | -50 | | | V |
| Emitter-base breakdown voltage | $V_{(BR)EBO}$ | $I_E = -100\mu\text{A}, I_C = 0$ | -5 | | | V |
| Collector cut-off current | I_{CBO} | $V_{CB} = -50\text{V}, I_E = 0$ | | | -0.1 | μA |
| Collector cut-off current | I_{CEO} | $V_{CE} = -50\text{V}, I_B = 0$ | | | -1 | μA |
| Emitter cut-off current | I_{EBO} | $V_{EB} = -5\text{V}, I_C = 0$ | | | -0.1 | μA |
| DC current gain | h_{FE} | $V_{CE} = -6\text{V}, I_C = -2\text{mA}$ | 130 | | 400 | |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | $I_C = -100\text{mA}, I_B = -10\text{mA}$ | | | -0.3 | V |
| Base-emitter saturation voltage | $V_{BE(sat)}$ | $I_C = -100\text{mA}, I_B = -10\text{mA}$ | | | -1.1 | V |
| Transition frequency | f_T | $V_{CE} = -10\text{V}, I_C = -1\text{mA}$ $f = 30\text{MHz}$ | 80 | | | MHz |

CLASSIFICATION OF h_{FE}

| Rank | L | H |
|-------|---------|---------|
| Range | 130-200 | 200-400 |





| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|-------|----------------------|-------|
| | Min | Max | Min | Max |
| A | 0.900 | 1.150 | 0.035 | 0.045 |
| A1 | 0.000 | 0.100 | 0.000 | 0.004 |
| A2 | 0.900 | 1.050 | 0.035 | 0.041 |
| b | 0.300 | 0.500 | 0.012 | 0.020 |
| c | 0.080 | 0.150 | 0.003 | 0.006 |
| D | 2.800 | 3.000 | 0.110 | 0.118 |
| E | 1.200 | 1.400 | 0.047 | 0.055 |
| E1 | 2.250 | 2.550 | 0.089 | 0.100 |
| e | 0.950 TYP | | 0.037 TYP | |
| e1 | 1.800 | 2.000 | 0.071 | 0.079 |
| L | 0.550 REF | | 0.022 REF | |
| L1 | 0.300 | 0.500 | 0.012 | 0.020 |
| θ | 0° | 8° | 0° | 8° |